Device Modeling Report

COMPONENTS:THYRISTOR
PART NUMBER:BTH151S-650R
MANUFACTURER: PHILIPS SEMICONDUCTOR

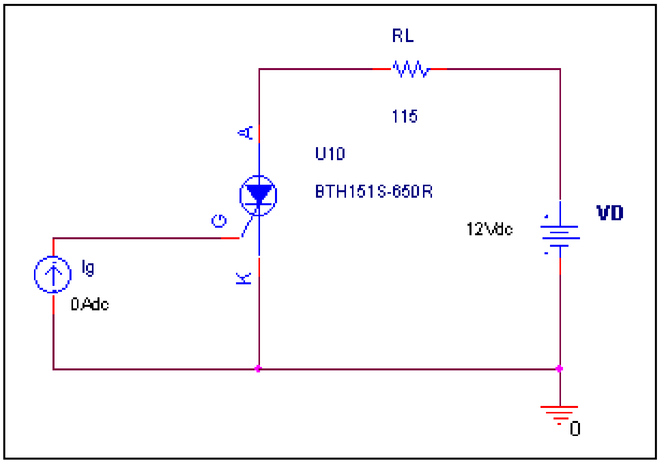
Bee Technologies Inc.

DIODE MODEL

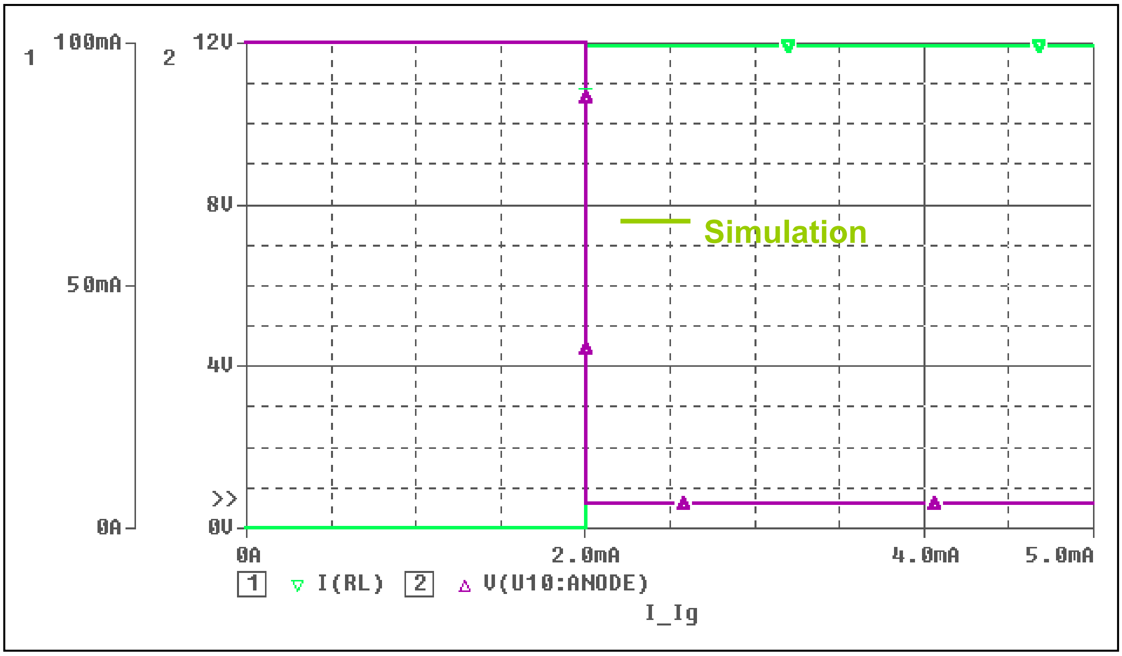
Pspice model Parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

IG-VT Characteristic

Evaluation Circuit



Simulation result

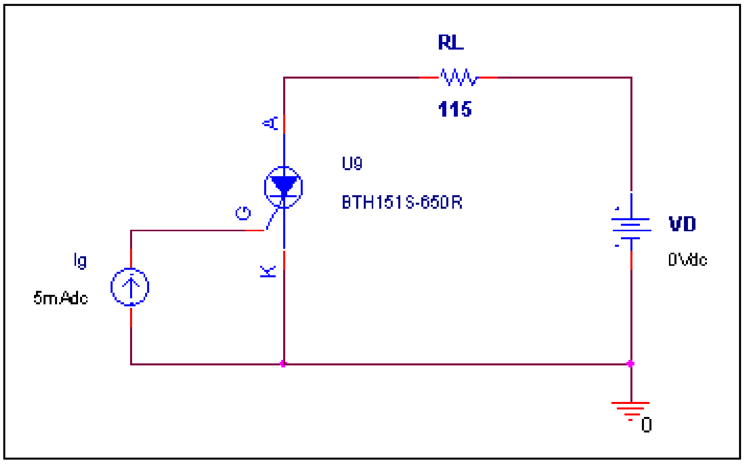


Comparison Table

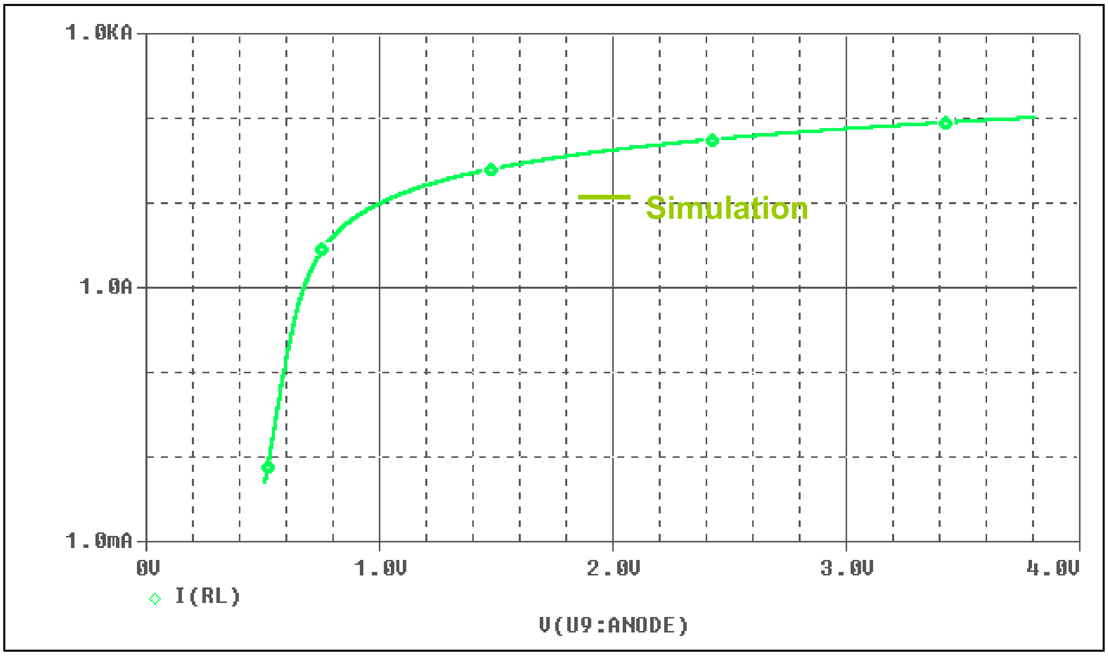
	Measurement	Simulation	% Error
IG_T (mA)	2	2.0044	0.22000
V_{GT} (V)	0.6	0.596	-0.66667

ITM-VTM Characteristic

Evaluation Circuit



Simulation result

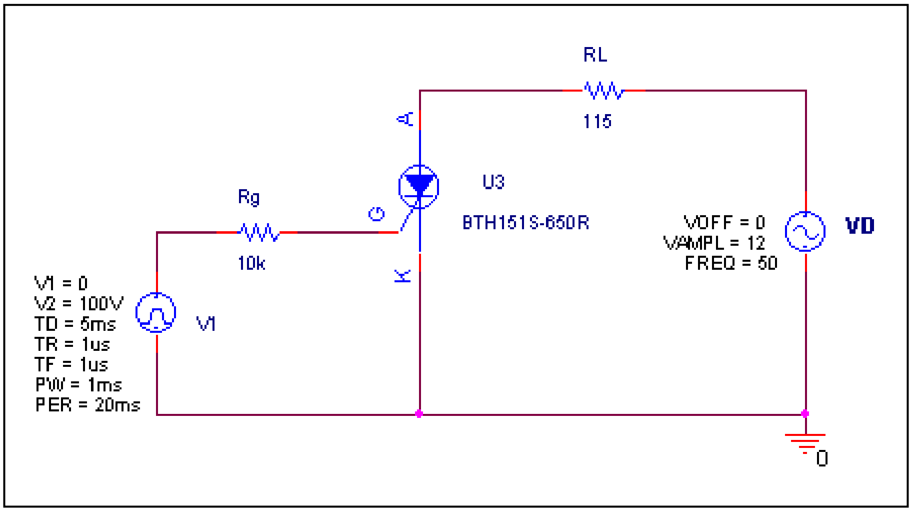


Comparison Table

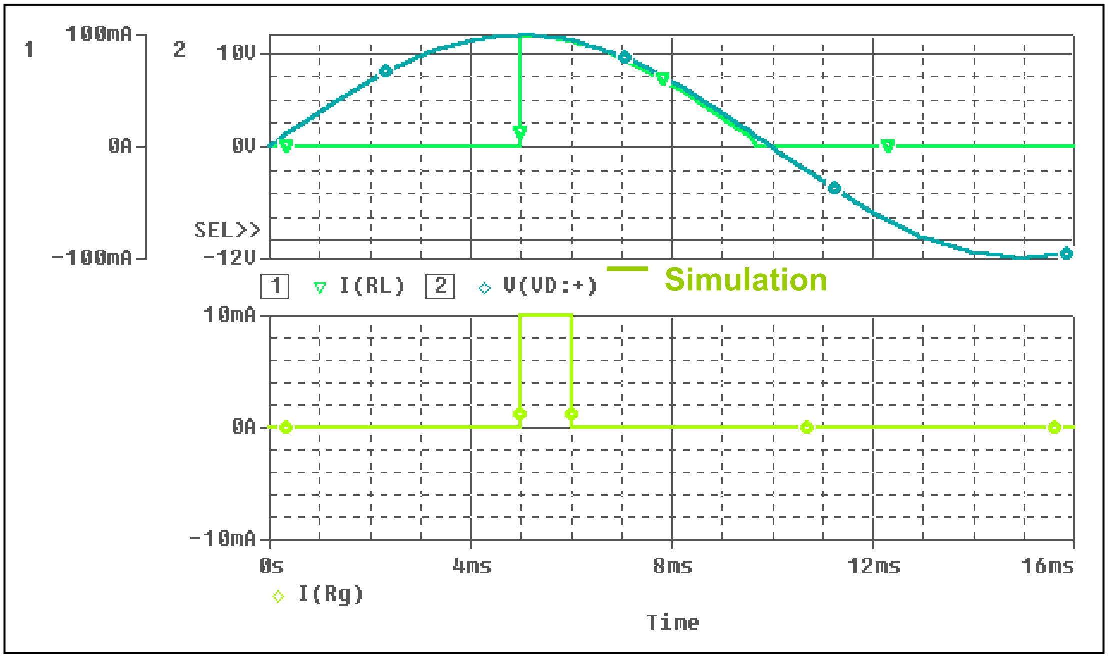
At ITM=23A	Measurement	Simulation	% Error
VTM(V)	1.4	1.4286	2.04286

Holding Characteristic (IH)

Evaluation Circuit



Simulation result

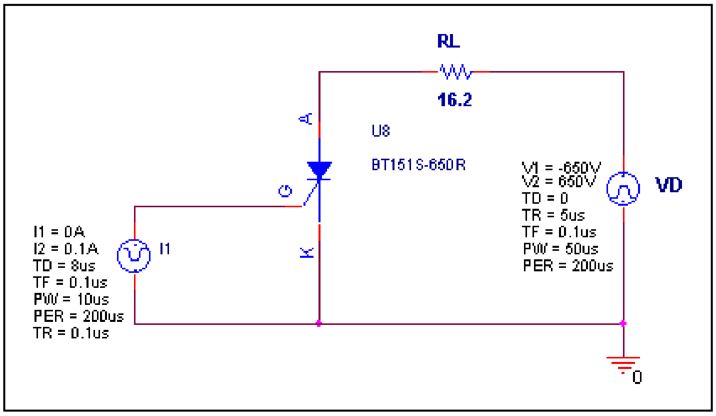


Comparison Table

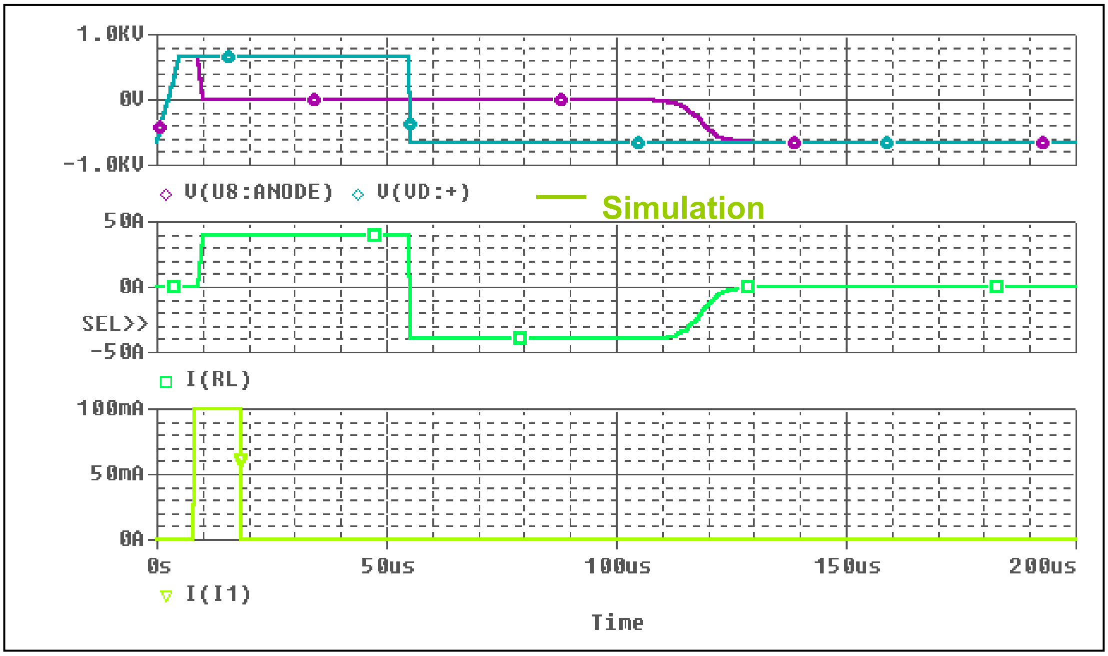
VD=12V	Measurement	Simulation	% Error
IH(mA)	7	6.8890	-1.58571

Switching Time Characteristic

Evaluation Circuit



Simulation result



Comparison Table

	Measurement	Simulation	%Error
Ton(us)	2	1.9958	-0.21000
Toff(us)	70	68.657	-1.91857